

In th Specification

At p. 1, before the "Technical Field" section, insert

--RELATED PATENT DATA

This patent resulted from a continuation application of U.S. Patent Application Serial No. 09/945,137, filed on August 30, 2001.--

Amendments to the Specification

Please add a new paragraph after paragraph [0014] on page 4 as follows:

Fig. 8 shows a cross sectional view of a substrate fragment according to an alternative aspect of the invention.

Please amend paragraph [0046] on page 20 as follows:

The methods described herein are not limited to formation of a single layer having a perovskite-type crystalline structure or a single composition for the perovskite-type crystalline structure. Different starting materials can be provided or different oxidation processing can occur to yield multiple layers of perovskite-type material having the same or different composition. Accordingly, a capacitor dielectric forming method includes forming a first alloy layer containing at least two metals over a capacitor electrode and forming a second alloy layer comprising at least two metals over the first alloy layer. The method includes oxidizing the first alloy layer and oxidizing the second alloy layer. The method also includes processing the first alloy layer to form a first capacitor dielectric layer having a perovskite-type crystalline structure and processing the second alloy layer to form a second capacitor dielectric layer having a perovskite-layer crystalline structure. The method may

include completion of processing the first alloy layer before forming the second alloy layer. The method may instead include oxidizing the first and second alloy layers together. The method can further include processing the first and second alloy layers together. Accordingly, Fig. 8 shows a capacitor construction 30 where dielectric 8 is replaced by a first dielectric 26 and a second dielectric 28. Outer dielectric 20 such as shown in Fig. 7 is over first and second dielectrics 26, 28.